



Single Wafer System to Enable High Volume Production of Highly-Efficient GaN Lighting Devices



Propel® enLight™ GaN MOCVD System

Clusterable platform accelerates the adoption of GaN-based advanced light emitting diodes

- > Unparalleled performance
- > Exceptional productivity
- > Best-in-class flexibility
- > Lowest cost of ownership



Veeco's enLight Advantage

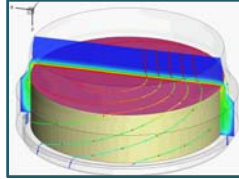
Veeco's new Propel enLight GaN MOCVD system is designed specifically for the high-volume high-performance, broadband superluminescent light emitting diodes industry. Featuring a single-wafer reactor platform capable of processing eight- and twelve-inch wafers, the enLight system deposits high-quality GaN films that result in highly-efficient power electronic devices.

Performance Advantages

Designed for Superior Thermal and Thickness Uniformity

TurboDisc® Single Wafer Reactor

- > High Velocity Laminar Flow
- > No leading / trailing edge effects



Rotating Disc Chamber: Iso-view

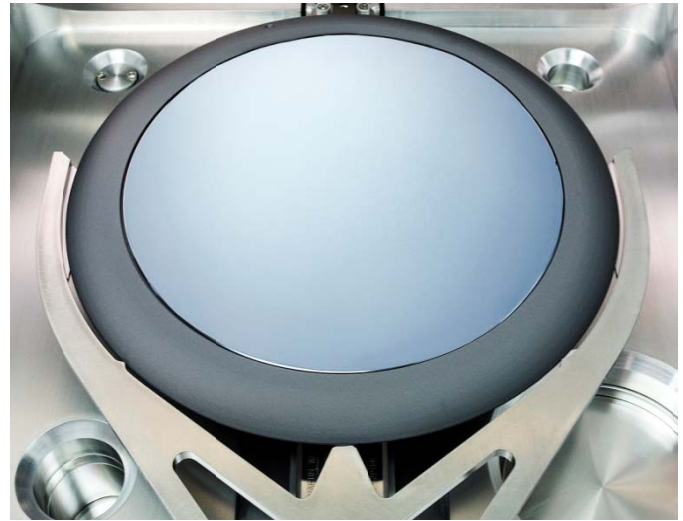
IsoFlange™ Technology

- > Optimized alkyl/hydride center injection for excellent inner zone uniformity
- > Improved alkyl spacing for better flow distribution across wafer carrier



SymmHeat™ Technology

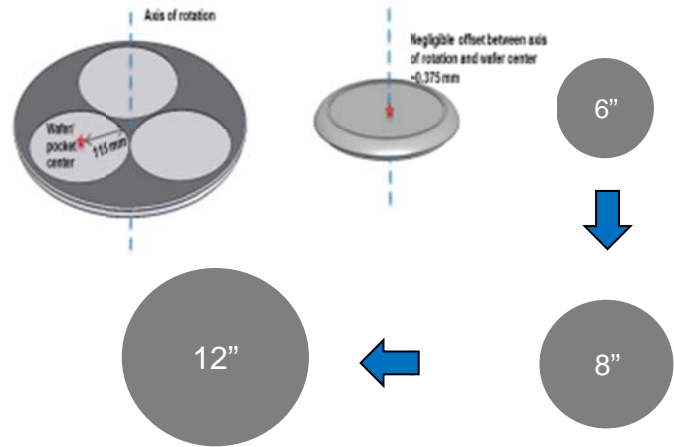
- > Concentric heating improves wafer bow control
- > No spindle means no center cold zone
- > Extends uniform temperature to the center and outer edge of the wafer carrier



Flexibility Advantages

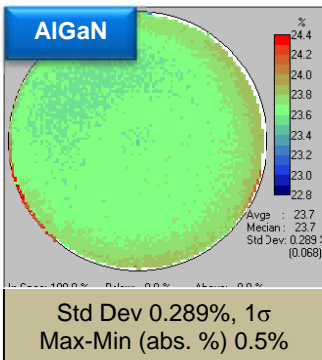
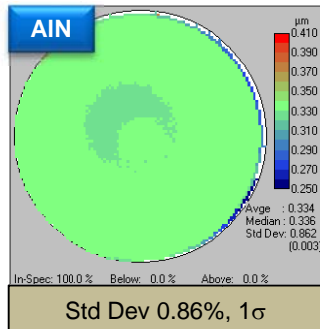
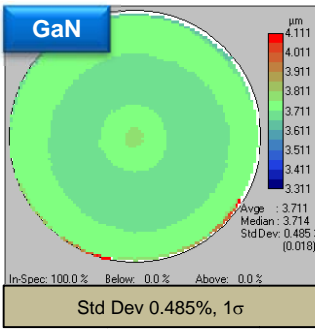
Extendable to 12" wafer size

- > Seamless process transfer to larger substrates



Productivity Advantages

Reduces recipe time to enable the maximum throughput



Excellent wafer-to-wafer and run-to-run uniformity without tuning

Cost of Ownership Advantages

8" substrate >20% lower than competition

